Sidewall slopes and roughness of SU-8 HARMST

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There is an error in the caption to Fig. 8 and the accompanying text. The reference to a 4 μm opening should be

read as 50 μm . Also in the caption to Fig. 8 the statement that “Diffraction at top of the resist is neglected as the mask and resist were in hard contact.” should be ignored as diffraction was in fact included in the calculation.

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